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## Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims:**

1. (original) A method comprising:

providing a first wafer having a stack structure of a first base substrate, a layer of relaxed film, and a first layer of strained film,

depositing a layer of oxide onto the layer of strained film to provide an adhesion surface to the first wafer;

providing a second wafer, the second wafer being a silicon on insulation (SOI) wafer having a stack structure of a second base substrate and a layer of oxidized film;

attaching the first and second wafers; and

heating the first and second wafers at a first temperature to cause a silicon dioxide (SiO<sub>2</sub>) adhesion of the first substrate to the second substrate.

- 2. (original) The method of claim 1 further comprising: implanting hydrogen onto the first wafer before depositing the layer of oxide onto the second layer of strained film to create an embrittled region in the layer of relaxed film.
- 3. (original) The method of claim 2 further comprising:

  heating the first and second wafers at a second temperature to delaminate the two
  wafers along the embrittled region to form the second wafer having the layer of relaxed film.
- 4. (original) The method of claim 3 further comprising:
  etching the relaxed film on the surface of the second wafer to expose the strained film.
- 5. (original) The method of claim 1 wherein the first and second base substrates are made of silicon material.

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- (previously presented) The method of claim 1 wherein the layer of relaxed film is a relaxed Silicon Germanium (SiGe) layer having a thickness in a range of approximately 0.1μm to 3.0μm.
- 7. (original) The method of claim 1 wherein the layer of oxide is deposited at a thickness range of approximately 50 to 3000A.
- 8. (original) The method of claim 2 wherein the hydrogen is implanted at an energy range of approximately 1 to 20keV.
- 9. (original) The method of claim 3 wherein the second temperature is higher than the first temperature.
- 10. (original) The method of claim 3 wherein the first temperature is in a range of approximately 100 °C to 300 °C.
- 11. (original) The method of claim 3 wherein the second temperature is in a range of 400 °C to 600 °C.
- 12. (original) The method of claim 1 further comprising:
  etching the first base substrate, and the layer of relaxed film to result in the strain
  of film on the surface of the SOI wafer.
- 13. (original) The method of claim 12 wherein the etching of the first layer of strained film comprises wet etching the layer of relaxed film.

14-19. (canceled)

20. (withdrawn) A method comprising: forming a relaxed layer on a silicon layer; forming a strained layer on the relaxed layer;

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creating an embrittled region in one of the relaxed and strained layers; and transferring the strained layer to top of a wafer by heat treatment, the wafer having a base substrate and an oxidized film.

- 21. (withdrawn) The method of claim 20 wherein forming a relaxed layer comprises: forming a relaxed silicon germanium (SiGe) layer having a thickness in a range of 0.1μm to 3.0μm.
  - 22. (withdrawn) The method of claim 20 wherein creating comprises: creating the embrittled region by an ion implantation.
- 23. (withdrawn) The method of claim 20 wherein creating comprises: creating the embrittled region by an ion implantation using an energy range of approximately 1 keV to 20 keV.
- 24. (withdrawn) The method of claim 20 wherein creating comprises: creating the embrittled region by an ion implantation using a dose range of approximately 1E16/cm<sup>3</sup> to 1E18/cm<sup>3</sup>.
- 25. (withdrawn) The method of claim 20 wherein transferring comprises:

  bonding the strained layer to the oxidized wafer by a first heat treatment in a range of approximately 100°C to 300°C; and

separating the strained layer from the relaxed layer at the embrittled region by a second heat treatment in a range of approximately 400°C to 600°C.